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In the Claims:

1 1. (currently amended) A light emitting device of a II-VI
2 group compound semiconductor formed on a compound
3 semiconductor substrate and having an active layer between
4 an n-type cladding layer and a p-type cladding layer,
5 comprising

6 [[a]] an i-type semiconductor barrier layer having a
7 band gap larger than a band gap of said p-type cladding
8 layer, provided between said active layer and said p-type
9 cladding layer.

1 2. (withdrawn) The semiconductor light emitting device
2 according to claim 1, wherein

3 said light emitting device of the II-VI group compound
4 is a ZnSe based light emitting device;

5 said n-type cladding layer is an n-type $Zn_{1-x}Mg_xS_ySe_{1-y}$
6 ($0 < x < 1$, $0 < y < 1$) layer; and

7 said p-type cladding layer is a p-type $Zn_{1-x}Mg_xS_ySe_{1-y}$
8 ($0 < x < 1$, $0 < y < 1$) layer.

1 3. (original) The semiconductor light emitting device
2 according to claim 1, wherein

3 magnitude of the band gap of said barrier layer is
4 larger by 0.025 eV to 0.5 eV than the band gap of said
5 p-type cladding layer.

1 4. (previously presented) The semiconductor light emitting
2 device according to claim 1, wherein

3 in the band gap of said barrier layer, energy of
4 valence band is approximately the same as or higher than
5 that of said p-type cladding layer, and energy of
6 conductive band is larger than that of said p-type cladding
7 layer.

1 5. (original) The semiconductor light emitting device
2 according to claim 1, wherein

3 said barrier layer is of a II-VI group compound
4 semiconductor containing Be.

1 6. (original) The semiconductor light emitting device
2 according to claim 5, wherein

3 said barrier layer is of $Zn_{1-x-y}Mg_xBe_ySe$ ($0 \leq x + y \leq 1$,
4 $0 < x$, $0 < y$).

1 7. (withdrawn) The semiconductor light emitting device
2 according to claim 1, wherein

3 said barrier layer is of $Zn_{1-x}Mg_xS_ySe_{1-y}$.

1 8. (withdrawn) The semiconductor light emitting device
2 according to claim 1, comprising

3 a semiconductor trap layer having a band gap smaller
4 than a band gap of said p-type cladding layer, provided
5 between said barrier layer and said p-type cladding layer.

1 **9.** (withdrawn) The semiconductor light emitting device
2 according to claim 8, having a multi-stacked structure in
3 which a plurality of double-layer-structure of said barrier
4 layer and said trap layer are stacked.

1 **10.** (withdrawn) The semiconductor light emitting device
2 according to claim 8, wherein
3 said trap layer is of ZnS_xSe_{1-x} ($0 \leq x \leq 0.1$).

1 **11.** (original) The semiconductor light emitting device
2 according to claim 1, wherein
3 said p-type cladding layer is formed of
4 $(Zn_{1-x}Cd_xS)_{1-z}(MgS_{1-y}Se_y)_z$ (where x, y, z satisfy $0 < x \leq 1$,
5 $0 \leq y \leq 1$, $0 \leq z < 1$).

1 **12.** (original) The semiconductor light emitting device
2 according to claim 1, wherein
3 thickness of said barrier layer is at least 5 nm and
4 at most thickness of said active layer.

1 **13.** (original) The semiconductor light emitting device
2 according to claim 1, wherein
3 an n-type ZnSe single crystal substrate is used as
4 said compound semiconductor substrate.

1 **14.** (original) The semiconductor light emitting device
2 according to claim 1, wherein

3 an n-type GaAs single crystal substrate is used as
4 said compound semiconductor substrate.

1 **15.** (original) The semiconductor light emitting device
2 according to claim 1, wherein

3 in a stacked structure including said compound
4 semiconductor substrate constituting said ZnSe based light
5 emitting device, deviation between a peak of X-ray
6 diffraction of a plane orientation used as an index of
7 distortion from said substrate and a peak of X-ray
8 diffraction of said plane orientation from said stacked
9 structure is at most 1000 seconds.

Claims **16 to 22** (cancelled).

1 **23.** (new) The semiconductor light emitting device according to
2 claim 1, wherein said barrier layer is a single monolayer
3 interposed between said active layer and said p-type
4 cladding layer.

1 **24.** (new) The semiconductor light emitting device according to
2 claim 1, wherein said barrier layer is disposed directly on
3 said active layer.

1 **25.** (new) The semiconductor light emitting device according to
2 claim 1, wherein said p-type cladding layer is disposed
3 directly on said barrier layer.